

L Number	Hits	Search Text	DB	Time stamp
-	1565	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)	USPAT	2003/11/30 03:11
-	841	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)	USPAT	2003/10/31 13:41
-	84	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi)	USPAT	2003/10/31 13:42
-	84	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous)	USPAT	2003/10/31 15:00
-	0	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous) and (RIE DRIE etch\$3)	USPAT	2003/10/31 13:44
-	19	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous) and (RIE DRIE etch\$3) and gyroscope	USPAT	2003/10/31 14:52
-	65	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous) and (RIE DRIE etch\$3) and vibrat\$3	USPAT	2003/10/31 14:52
-	8	((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous) and (RIE DRIE etch\$3) not (((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si) and (epitaxially epitaxy epitaxial epi) and (anodize anodization porous) and (RIE DRIE etch\$3) and vibrat\$3) and ((deep with (RIE etch\$3) DRIE)	USPAT	2003/10/31 15:09

-	57	<p>(((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))</p>	USPAT	2003/10/31 15:13
-	9	<p>(((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not ((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))) and ring</p>	USPAT	2003/10/31 15:27

-	48	((((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))) and ring)	USPAT	2003/10/31 15:27
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-	21	<p> ((((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) not (((((((light lightly) and (heavy heavily)) with (dope doped dopant doping) with (silicon si)) and (epitaxially epitaxy epitaxial epi)) and (anodize anodization porous)) and (RIE DRIE etch\$3)) and vibrat\$3)) and ((deep with (RIE etch\$3)) DRIE))) and ring)) and (bury buried burying) same (dope doped dopant doping layer) </p>	USPAT	2003/10/31 15:30
-	1	("6602427").PN.	USPAT	2003/11/30 03:11
-	5	("5408319" "5589689" "6147756" "6215577" "6271052").PN.	USPAT	2003/11/30 03:11
-	0	6602427.URPN.	USPAT	2003/11/30 03:11